Philippe Boucaud

List of Publications by Year
in descending order

264	6,427	46918	95083
papers	citations	47 h-index	68 g-index

264	264	264	3476
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Band structure and optical gain of tensile-strained germanium based on a 30 band kâ‹…p formalism. Journal of Applied Physics, 2010, 107, .	1.1	197
2	Ultra-low-threshold continuous-wave and pulsed lasing in tensile-strained GeSn alloys. Nature Photonics, 2020, 14, 375-382.	15.6	145
3	Intraband absorption in n-doped InAs/GaAs quantum dots. Applied Physics Letters, 1997, 71, 2785-2787.	1.5	142
4	Third-harmonic generation in InAs/GaAs self-assembled quantum dots. Physical Review B, 1999, 59, 9830-9833.	1.1	140
5	Vertically self-organized Ge/Si(001) quantum dots in multilayer structures. Physical Review B, 1999, 60, 5851-5857.	1.1	135
6	Long-wavelength (â‰ˆ15.5â€‰Î¼m) unipolar semiconductor laser in GaAs quantum wells. Applied Physics Letters, 1997, 71, 3619-3621.	1.5	134
7	Control of direct band gap emission of bulk germanium by mechanical tensile strain. Applied Physics Letters, 2010, 96, .	1.5	129
8	Long Polaron Lifetime in InAs/GaAs Self-Assembled Quantum Dots. Physical Review Letters, 2002, 88, 177402.	2.9	119
9	Enhanced photoluminescence of heavily n-doped germanium. Applied Physics Letters, 2009, 94, .	1.5	109
10	Detailed analysis of secondâ€harmonic generation near 10.6 Î¼m in GaAs/AlGaAs asymmetric quantum wells. Applied Physics Letters, 1990, 57, 215-217.	1.5	106
11	Engineering strained silicon on insulator wafers with the Smart CutTM technology. Solid-State Electronics, 2004, 48, 1285-1296.	0.8	106
12	Bandâ€edge and deep level photoluminescence of pseudomorphic Si1â^'xâ^'yGexCyalloys. Applied Physics Letters, 1994, 64, 875-877.	1.5	103
13	Infrared spectroscopy of intraband transitions in self-organized InAs/GaAs quantum dots. Journal of Applied Physics, 1997, 82, 3396-3401.	1.1	99
14	Tensile Ge microstructures for lasing fabricated by means of a silicon complementary metal-oxide-semiconductor process. Optics Express, 2014, 22, 399.	1.7	96
15	Growth and characterization of strain compensated Si1â^'xâ^'y epitaxial layers. Materials Letters, 1993, 18, 57-60.	1.3	83
16	In-plane polarized intraband absorption in InAs/GaAs self-assembled quantum dots. Physical Review B, 1998, 58, 10562-10567.	1.1	83
17	Optical gain in single tensile-strained germanium photonic wire. Optics Express, 2011, 19, 17925.	1.7	83
18	Strain analysis in SiN/Ge microstructures obtained via Si-complementary metal oxide semiconductor compatible approach. Journal of Applied Physics, 2013, 113, .	1.1	82

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19	Intraband absorption in Ge/Si self-assembled quantum dots. Applied Physics Letters, 1999, 74, 401-403.	1.5	79
20	Midinfrared absorption and photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2001, 78, 2327-2329.	1.5	78
21	Recent advances in germanium emission [Invited]. Photonics Research, 2013, 1, 102.	3.4	76
22	Tensile-strained germanium microdisks. Applied Physics Letters, 2013, 102, 221112.	1.5	75
23	Infrared second-order optical susceptibility in InAs/GaAs self-assembled quantum dots. Physical Review B, 2000, 61, 5562-5570.	1.1	74
24	Band-edge alignment ofSiGeâˆ•Siquantum wells andSiGeâˆ•Siself-assembled islands. Physical Review B, 2006, 73, .	1.1	73
25	Two-dimensional photonic crystals with large complete photonic band gaps in both TE and TM polarizations. Optics Express, 2008, 16, 12278.	1.7	73
26	Near-infrared waveguide photodetector with Ge/Si self-assembled quantum dots. Applied Physics Letters, 2002, 80, 509-511.	1.5	72
27	Allâ€Around SiN Stressor for High and Homogeneous Tensile Strain in Germanium Microdisk Cavities. Advanced Optical Materials, 2015, 3, 353-358.	3.6	72
28	Nucleation and growth of self-assembled Ge/Si(001) quantum dots. Physical Review B, 1998, 58, 13115-13120.	1.1	65
29	Electroluminescence of Ge/Si self-assembled quantum dots grown by chemical vapor deposition. Applied Physics Letters, 2000, 77, 1822.	1.5	65
30	Infrared photodetection with semiconductor self-assembled quantum dots. Comptes Rendus Physique, 2003, 4, 1133-1154.	0.3	61
31	High quality tensile-strained n-doped germanium thin films grown on InGaAs buffer layers by metal-organic chemical vapor deposition. Applied Physics Letters, 2011, 98, .	1.5	58
32	Control of tensile strain and interdiffusion in Ge/Si(001) epilayers grown by molecular-beam epitaxy. Journal of Applied Physics, 2013, 114, .	1.1	58
33	Phase-matched second harmonic generation with on-chip GaN-on-Si microdisks. Scientific Reports, 2016, 6, 34191.	1.6	58
34	Midinfrared photoconductivity of Ge/Si self-assembled quantum dots. Applied Physics Letters, 2000, 77, 3224-3226.	1.5	57
35	Deep-UV nitride-on-silicon microdisk lasers. Scientific Reports, 2016, 6, 21650.	1.6	57
36	Second-harmonic generation resonant withs-ptransition in InAs/GaAs self-assembled quantum dots. Physical Review B, 2001, 63, .	1.1	56

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37	Two-dimensional photonic crystals with Ge/Si self-assembled islands. Applied Physics Letters, 2003, 83, 2509-2511.	1.5	54
38	High quality factor nitride-based optical cavities: microdisks with embedded GaN/Al(Ga)N quantum dots. Optics Letters, 2011, 36, 2203.	1.7	54
39	Control of tensile strain in germanium waveguides through silicon nitride layers. Applied Physics Letters, 2012, 100, 201104.	1.5	54
40	Direct Band Gap Germanium Microdisks Obtained with Silicon Nitride Stressor Layers. ACS Photonics, 2016, 3, 443-448.	3.2	54
41	Photoluminescence of strained Si1â^'yCy alloys grown at low temperature. Applied Physics Letters, 1995, 66, 70-72.	1.5	53
42	Optical recombination from excited states in Ge/Si self-assembled quantum dots. Physical Review B, 2001, 64, .	1.1	51
43	Temperature dependence of intersublevel absorption in InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2002, 80, 4620-4622.	1.5	51
44	Direct and indirect band gap room temperature electroluminescence of Ge diodes. Journal of Applied Physics, 2010, 108, 023105.	1.1	51
45	Quality factor of Si-based photonic crystal L3 nanocavities probed with an internal source. Optics Express, 2008, 16, 8780.	1.7	49
46	Impact of tensile strain on low Sn content GeSn lasing. Scientific Reports, 2019, 9, 259.	1.6	49
47	Saturation of intraband absorption and electron relaxation time in n-doped InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 1998, 73, 3818-3821.	1.5	48
48	Intersubband stimulated emission in GaAs/AlGaAs quantum wells: Pump-probe experiments using a two-color free-electron laser. Applied Physics Letters, 1997, 70, 3197-3199.	1.5	47
49	Germanium microlasers on metallic pedestals. APL Photonics, 2018, 3, .	3.0	46
50	Strain compensated heterostructures in the Si1â^'xâ^'yGexCy ternary system. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1994, 12, 1015-1019.	0.9	45
51	Ultraweak-Absorption Microscopy of a Single Semiconductor Quantum Dot in the Midinfrared Range. Physical Review Letters, 2007, 99, 217404.	2.9	44
52	Reduced Lasing Thresholds in GeSn Microdisk Cavities with Defect Management of the Optically Active Region. ACS Photonics, 2020, 7, 2713-2722.	3.2	42
53	Photoluminescence up-conversion induced by intersubband absorption in asymmetric coupled quantum wells. Physical Review Letters, 1993, 70, 1018-1021.	2.9	41
54	Saturation of second-harmonic generation in GaAsâ€"AlGaAs asymmetric quantum wells. Optics Letters, 1991, 16, 199.	1.7	39

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55	Secondâ€harmonic generation in asymmetric Si/SiGe quantum wells. Applied Physics Letters, 1994, 65, 2969-2971.	1.5	38
56	Nanocrystalline diamond photonics platform with high quality factor photonic crystal cavities. Applied Physics Letters, 2012, 101, .	1.5	38
57	III-Nitride-on-silicon microdisk lasers from the blue to the deep ultra-violet. Applied Physics Letters, 2016, 109, .	1.5	38
58	Investigation of mid-infrared intersubband stimulated gain under optical pumping in GaAs/AlGaAs quantum wells. Journal of Applied Physics, 1998, 83, 2920-2926.	1.1	35
59	Strain and composition of capped Ge/Si self-assembled quantum dots grown by chemical vapor deposition. Applied Physics Letters, 2000, 77, 370-372.	1.5	35
60	Two-dimensional photonic crystals with pure germanium-on-insulator. Optics Communications, 2008, 281, 846-850.	1.0	35
61	Photoluminescence and intersubband absorption spectroscopy of interdiffused Si/SiGe quantum wells. Journal of Applied Physics, 1996, 80, 1414-1421.	1.1	33
62	Photoluminescence study of a bimodal size distribution of Ge/Si(001) quantum dots. Physical Review B, 2001, 63, .	1.1	33
63	Near-infrared gallium nitride two-dimensional photonic crystal platform on silicon. Applied Physics Letters, 2014, 105, .	1.5	33
64	Comparison between 6-band and 14-bandkâ‹…pformalisms in SiGe/Si heterostructures. Physical Review B, 2003, 68, .	1.1	32
65	Stimulated Raman scattering in silicon photonic crystal waveguides under continuous excitation. Physical Review B, 2010, 82, .	1.1	32
66	AlN photonic crystal nanocavities realized by epitaxial conformal growth on nanopatterned silicon substrate. Applied Physics Letters, 2011, 98, 261106.	1.5	32
67	Blue Microlasers Integrated on a Photonic Platform on Silicon. ACS Photonics, 2018, 5, 3643-3648.	3.2	32
68	Strain-driven modification of the Ge/Si growth mode in stacked layers: a way to produce Ge islands having equal size in all layers. Thin Solid Films, 2000, 369, 43-48.	0.8	31
69	Optimized design for 2 Ã— 106 ultra-high Q silicon photonic crystal cavities. Optics Communications, 2010, 283, 4387-4391.	1.0	31
70	Observation of infrared intersubband emission in optically pumped quantum wells. Electronics Letters, 1995, 31, 912-913.	0.5	30
71	Midinfrared second-harmonic generation in p-type InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 1999, 75, 835-837.	1.5	30
72	Probing photonic crystals on silicon-on-insulator with Geâˆ•Si self-assembled islands as an internal source. Journal of Applied Physics, 2006, 99, 023103.	1.1	30

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73	High quality factor AlN nanocavities embedded in a photonic crystal waveguide. Applied Physics Letters, 2012, 100, 191104.	1.5	29
74	Midinfrared absorption measured at a Î»/400 resolution with an atomic force microscope. Optics Express, 2009, 17, 10887.	1.7	28
75	Intersubband mid-infrared emission in optically pumped quantum wells. Superlattices and Microstructures, 1996, 19, 69-79.	1.4	27
76	Metal organic vapor phase epitaxy of InAsP/InP(001) quantum dots for 1.55Î¼m applications: Growth, structural, and optical properties. Journal of Applied Physics, 2008, 104, 043504.	1.1	27
77	High-frequency self-induced oscillations in a silicon nanocavity. Optics Express, 2013, 21, 13626.	1.7	27
78	Intermixing of GaInP/GaAs multiple quantum wells. Applied Physics Letters, 1993, 62, 178-180.	1.5	26
79	Saturation of THz-frequency intraband absorption in InAs/GaAs quantum dot molecules. Applied Physics Letters, 2000, 77, 510-512.	1.5	25
80	Siliconâ€“onâ€“insulator waveguide photodetector with Ge/Si self-assembled islands. Journal of Applied Physics, 2002, 92, 1858-1861.	1.1	25
81	Realization of heterostructures by pulsed laser induced epitaxy of C+ implanted pseudomorphic SiGe films and of a-SiGeC: H films deposited on Si(100). Journal of Crystal Growth, 1995, 157, 436-441.	0.7	24
82	Two-dimensional photonic crystals with germanium on insulator obtained by a condensation method. Applied Physics Letters, 2008, 93, .	1.5	24
83	Compositionally asymmetrical multiquantum wells: â€œPseudo-moleculesâ€•for giant optical nonlinearities in the infrared (9â€“11 Î¼m). Superlattices and Microstructures, 1990, 8, 369-374.	1.4	23
84	Ge/Si self-assembled quantum dots grown on Si(001) in an industrial high-pressure chemical vapor deposition reactor. Journal of Applied Physics, 1999, 86, 1145-1148.	1.1	23
85	Deterministic measurement of the Purcell factor in microcavities through Raman emission. Physical Review A, 2010, 81, .	1.0	23
86	Resonant second harmonic generation in a gallium nitride two-dimensional photonic crystal on silicon. Applied Physics Letters, 2015, 106, .	1.5	23
87	Near-infrared III-nitride-on-silicon nanophotonic platform with microdisk resonators. Optics Express, 2016, 24, 9602.	1.7	23
88	First demonstration of room temperature intersubband-interband double-resonance spectroscopy of GaAs/AlGaAs quantum wells. IEEE Photonics Technology Letters, 1990, 2, 398-400.	1.3	22
89	Influence of interface phonons on intersubband scattering in asymmetric coupled quantum wells. Physical Review B, 1993, 47, 12949-12952.	1.1	22
90	Strong 1.3â€“1.5 Î¼m luminescence from Ge/Si self-assembled islands in highly confining microcavities on silicon on insulator. Journal of Applied Physics, 2004, 96, 997-1000.	1.1	22

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91	Enhanced spontaneous Raman scattering in silicon photonic crystal waveguides on insulator. Optics Express, 2009, 17, 3500.	1.7	22
92	Homogeneous broadening of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>S</mml:mi></mml:mrow></mml:math>to<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>P</mml:mi></mml:mrow></mml:math>transition in InGaAs/GaAs quantum dots measured by infrared absorption imaging with nanoscale resolution. Physical Review B, 2011, 83, .	1.1	22
93	Light emission from strained germanium. Nature Photonics, 2013, 7, 162-162.	15.6	22
94	Molecular-beam epitaxial growth of tensile-strained and n-doped Ge/Si(001) films using a GaP decomposition source. Thin Solid Films, 2014, 557, 70-75.	0.8	22
95	Electroluminescence spectroscopy of AlGaAs/InGaAs and AlGaAs/GaAs highâ€electronâ€mobility transistors. Journal of Applied Physics, 1995, 77, 2184-2189.	1.1	21
96	Mid-infrared intersublevel absorption of vertically electronically coupled InAs quantum dots. Applied Physics Letters, 2005, 87, 173113.	1.5	21
97	Intersubband absorption of GaAs/AlGaAs quantum wells in MBE grown mid-infrared slab waveguides. IEEE Photonics Technology Letters, 1990, 2, 181-183.	1.3	20
98	Recombination processes in SiGe/Si quantum wells measured by photoinduced absorption spectroscopy. Physical Review B, 1997, 56, 15734-15739.	1.1	20
99	All-silicon photonic crystal photoconductor on silicon-on-insulator at telecom wavelength. Optics Express, 2010, 18, 23965.	1.7	20
100	Tensile-strained germanium microdisk electroluminescence. Optics Express, 2015, 23, 6722.	1.7	20
101	Tensile-strained germanium microdisks with circular Bragg reflectors. Applied Physics Letters, 2016, 108, .	1.5	20
102	Efficient second harmonic generation in low-loss planar GaN waveguides. Optics Express, 2017, 25, 23035.	1.7	20
103	III-nitride on silicon electrically injected microrings for nanophotonic circuits. Optics Express, 2019, 27, 11800.	1.7	20
104	Effect of increasing thickness on tensile-strained germanium grown on InGaAs buffer layers. Journal of Applied Physics, 2013, 113, 183508.	1.1	19
105	Schottky MSM junctions for carrier depletion in silicon photonic crystal microcavities. Optics Express, 2013, 21, 10324.	1.7	19
106	Resonant excitation of intraband absorption in InAs/GaAs self-assembled quantum dots. Journal of Applied Physics, 1998, 84, 4356-4362.	1.1	18
107	Temperature dependence of the absorption saturation relaxation time in light- and heavy-ion-irradiated bulk GaAs. Applied Physics Letters, 2002, 80, 4711-4713.	1.5	18
108	High quality factor in a two-dimensional photonic crystal cavity on silicon-on-insulator. Optics Letters, 2011, 36, 1749.	1.7	18

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109	GeSnOI mid-infrared laser technology. Light: Science and Applications, 2021, 10, 232.	7.7	18
110	Photoinduced intersubband absorption in Si/SiGe quantum wells. Applied Physics Letters, 1995, 67, 2948-2950.	1.5	17
111	Room temperature infrared intersubband photoluminescence in GaAs quantum wells. Applied Physics Letters, 1997, 70, 1345-1347.	1.5	17
112	Midinfrared unipolar photoluminescence in InAs/GaAs self-assembled quantum dots. Physical Review B, 1999, 60, 15589-15592.	1.1	17
113	Dephasing of intersublevel polarizations in InAs/GaAs self-assembled quantum dots. Physical Review B, 2002, 66, .	1.1	17
114	Intersublevel polaron laser with InAsâˆ•GaAs self-assembled quantum dots. Applied Physics Letters, 2006, 88, 063106.	1.5	16
115	Quality factor control of Si-based two-dimensional photonic crystals with a Bragg mirror. Applied Physics Letters, 2006, 88, 091122.	1.5	16
116	Up to 300â€…K lasing with GeSn-On-Insulator microdisk resonators. Optics Express, 2022, 30, 3954.	1.7	16
117	Terahertz-frequency electronic coupling in vertically coupled quantum dots. Applied Physics Letters, 2000, 77, 4356-4358.	1.5	15
118	Kinetics of the heteroepitaxial growth of Ge on Si(001). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1251.	1.6	15
119	Germanium-based nanophotonic devices: Two-dimensional photonic crystals and cavities. Thin Solid Films, 2008, 517, 121-124.	0.8	15
120	Surface-sensitive diamond photonic crystals for high-performance gas detection. Optics Letters, 2016, 41, 4360.	1.7	15
121	Silicon-on-insulator and SiGe waveguide photodetectors with Ge/Si self-assembled islands. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 523-527.	1.3	14
122	Intersublevel transitions in self-assembled quantum dots. Comptes Rendus Physique, 2008, 9, 840-849.	0.3	14
123	Aluminum nitride photonic crystals and microdiscs for ultra-violet nanophotonics. Advances in Natural Sciences: Nanoscience and Nanotechnology, 2014, 5, 023001.	0.7	14
124	Imaging of Photonic Crystal Localized Modes through Third-Harmonic Generation. ACS Photonics, 2016, 3, 1240-1247.	3.2	14
125	Analysis of low-threshold optically pumped III-nitride microdisk lasers. Applied Physics Letters, 2020, 117, .	1.5	14
126	Photoluminescence study of bandâ€gap alignment of intermixed InAsP/InGaAsP superlattices. Journal of Applied Physics, 1995, 78, 1944-1947.	1.1	13

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127	Effect of the bimodal size distribution on the optical properties of self-assembled Ge/Si(001) quantum dots. Thin Solid Films, 2000, 380, 78-81.	0.8	13
128	Aspects of Ge/Si self-assembled quantum dots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 36-44.	1.7	13
129	Photoluminescence of a tensilely strained silicon quantum well on a relaxed SiGe buffer layer. Applied Physics Letters, 2004, 85, 46-48.	1.5	13
130	Monolithic integration of ultraviolet microdisk lasers into photonic circuits in a III-nitride-on-silicon platform. Optics Letters, 2020, 45, 4276.	1.7	13
131	Intersubband relaxation time in the valence band of Si/Si1â^'xGex quantum wells. Applied Physics Letters, 1996, 69, 3069-3071.	1.5	12
132	Intersubband photoluminescence of GaAs quantum wells under selective interband excitation. Applied Physics Letters, 1997, 71, 1183-1185.	1.5	12
133	Vertical ordering in multilayers of self-assembled Ge/Si(001) quantum dots. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1259.	1.6	12
134	Analysis of optical gain threshold in n-doped and tensile-strained germanium heterostructure diodes. Journal of Applied Physics, 2015, 118, 125704.	1.1	12
135	Making germanium, an indirect band gap semiconductor, suitable for light-emitting devices. Advances in Natural Sciences: Nanoscience and Nanotechnology, 2015, 6, 015013.	0.7	12
136	High-performance and power-efficient 2Ã—2 optical switch on Silicon-on-Insulator. Optics Express, 2015, 23, 24163.	1.7	12
137	Low temperature electroluminescence spectroscopy of high electron mobility transistors on InP. Journal of Applied Physics, 1996, 80, 464-469.	1.1	11
138	Molecular beam epitaxy growth of Ge[sub 1â^'y]C[sub y] alloys on Si (100) with high carbon contents. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1301.	1.6	11
139	Photoconductivity of Ge/Si quantum dot photodetectors. Infrared Physics and Technology, 2003, 44, 513-516.	1.3	11
140	1.5Î¼m room-temperature emission of square-lattice photonic-crystal waveguide lasers with a single line defect. Applied Physics Letters, 2005, 86, 151111.	1.5	11
141	Demonstration of critical coupling in an active III-nitride microdisk photonic circuit on silicon. Scientific Reports, 2019, 9, 18095.	1.6	11
142	Growth of Si 1 â^' x â^' y Ge x C y multi-quantum wells: structural and optical properties. Thin Solid Films, 1996, 278, 114-117.	0.8	10
143	Distributed feedback regime of photonic crystal waveguide lasers at 1.5Î¼m. Applied Physics Letters, 2004, 85, 5502-5504.	1.5	10
144	Ge islands and photonic crystals for Si-based photonics. Optical Materials, 2005, 27, 792-798.	1.7	10

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145	Distributed feedback-like laser emission in photonic crystal waveguides on InP substrate. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1180-1186.	1.9	10
146	Ultrafast resonant terahertz response of excitons in semiconductor quantum dots. Physical Review B, 2008, 77, .	1.1	10
147	Optical Analysis of pâ€Type Surface Conductivity in Diamond with Slotted Photonic Crystals. Advanced Optical Materials, 2013, 1, 963-970.	3.6	10
148	RTCVD growth and characterization of SiGeC multi-quantum wells. Thin Solid Films, 1997, 294, 125-128.	0.8	9
149	Photoluminescence of self-assembled Ge dots grown by ultra-high-vacuum chemical vapor deposition. Thin Solid Films, 1998, 336, 240-243.	0.8	9
150	Midinfrared Photoconductivity in Ge/Si Self-Assembled Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 233-236.	0.7	9
151	Ge/Si self-assembled islands integrated in 2D photonic crystals microcavities for realisation of silicon-based light-emitting devices. , 2004, 5450, 369.		9
152	Pumpâ€“probe analysis of polaron decay in InAs/GaAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 59-62.	1.3	9
153	Thermal emission of midinfrared GaAs photonic crystals. Physical Review B, 2008, 78, .	1.1	9
154	Absorption and resonant dispersion associated with normal incidence intersubband transitions in Si/SiGe quantum wells. Applied Physics Letters, 1995, 67, 3462-3464.	1.5	8
155	On the formation of self-assembled Ge/Si(001) quantum dots. Journal of Crystal Growth, 1999, 201-202, 1212-1217.	0.7	8
156	Heterostructures of pseudomorphic Ge[sub 1â^'y]C[sub y] and Ge[sub 1â^'xâ^'y]Si[sub x]C[sub y] alloys grown on Ge (001) substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1728.	1.6	8
157	GaN quantum dots in (Al,Ga)N-based Microdisks. Journal of Physics: Conference Series, 2010, 210, 012005.	0.3	8
158	Schottky electroluminescent diodes with n-doped germanium. Applied Physics Letters, 2014, 104, .	1.5	8
159	Low-loss GaN-on-insulator platform for integrated photonics. Optics Express, 2022, 30, 20737.	1.7	8
160	Growth and in situ ellipsometric analysis of Si1-xGex alloys deposited by chemical beam epitaxy. Journal of Electronic Materials, 1994, 23, 565-568.	1.0	7
161	Deep erbium-ytterbium implantation codoping of low-loss silicon oxynitride waveguides. Electronics Letters, 1995, 31, 636.	0.5	7
162	Raman spectroscopy of Si1 â^' x â^' yGexCy layers obtained by pulsed laser induced epitaxy. Applied Surface Science, 1996, 106, 171-178.	3.1	7

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163	Electroluminescence of composite channel InAlAs/InGaAs/InP/InAlAs high electron mobility transistor. Journal of Applied Physics, 2000, 87, 2548-2552.	1.1	7
164	Electromodulation of the interband and intraband absorption of Ge/Si self-assembled islands. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 450-454.	1.3	7
165	Fast decoherence of slowly relaxing polarons in semiconductor InAs quantum dots. Europhysics Letters, 2005, 70, 390-396.	0.7	7
166	Resonant coupling of quantum dot intersublevel transitions with midinfrared photonic crystal modes. Applied Physics Letters, 2009, 95, 041108.	1.5	7
167	Interference effects on bound-to-continuum quantum dot absorption. Journal of Applied Physics, 2010, 107, 083102.	1.1	7
168	High quality factor photonic resonators for nitride quantum dots. Physica Status Solidi (B): Basic Research, 2012, 249, 449-454.	0.7	7
169	Q factor limitation at short wavelength (around 300â€‰nm) in III-nitride-on-silicon photonic crystal cavities. Applied Physics Letters, 2017, 111, 131103.	1.5	7
170	GÃ©nÃ©ration de second-harmonique dans les puits quantiques asymetriques GaAs-AlGaAs. Journal De Physique III, 1991, 1, 13-28.	0.3	7
171	Influence of surface roughness on the lasing characteristics of optically pumped thin-film GaN microdisks. Optics Letters, 2022, 47, 1521.	1.7	7
172	Deep high-dose erbium implantation of low-loss silicon oxynitride waveguides. Electronics Letters, 1994, 30, 1850-1852.	0.5	6
173	Ion beam-induced interfacial growth in Si and silicides. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 206-215.	0.6	6
174	Laser damage of free-standing nanometer membranes. Journal of Applied Physics, 2017, 122, 215303.	1.1	6
175	Solving thermal issues in tensile-strained Ge microdisks. Optics Express, 2018, 26, 28376.	1.7	6
176	Laser diode modulation of 10.6 Î¼m radiation in GaAs/AlGaAs quantum wells. Electronics Letters, 1990, 26, 1531.	0.5	5
177	Schottky Diodes on Si_{1-x-y}Ge_xC_y Alloys.. Materials Research Society Symposia Proceedings, 1995, 379, 137.	0.1	5
178	Optical properties of bulk and multi-quantum well SiGe: C heterostructures. Journal of Crystal Growth, 1995, 157, 410-413.	0.7	5
179	Photoinduced infrared spectroscopy of bound-to-bound and bound-to-continuum transitions in SiGe/Si quantum wells. Superlattices and Microstructures, 1996, 19, 33-38.	1.4	5
180	Intersubband absorption in Si/Si1â^'xâ^'yGexCy quantum wells. Applied Physics Letters, 1996, 69, 1734-1736.	1.5	5

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